FIG.1

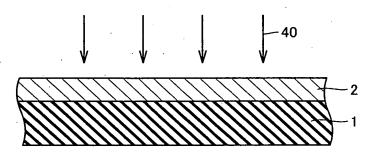


FIG.2

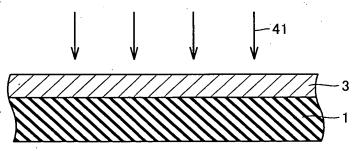


FIG.3

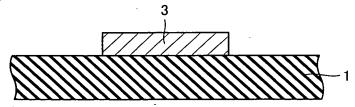


FIG.4

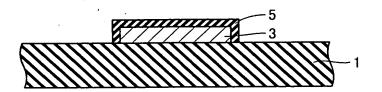


FIG.5

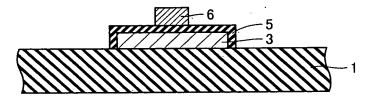
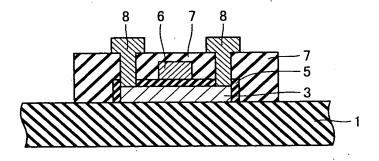
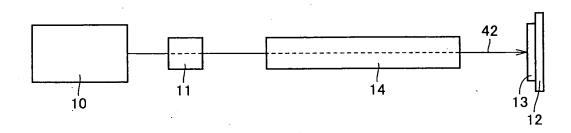


FIG.6



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Atty Docket No.: 403373
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FIG.7



Title: FABRICATING METHOD OF SEMICONDUCTOR DEVICE Inventors: INOUE et al.
Atty Docket No.: 403373
Leydig, Voit & Mayer 202-737-6770

FIG.8A

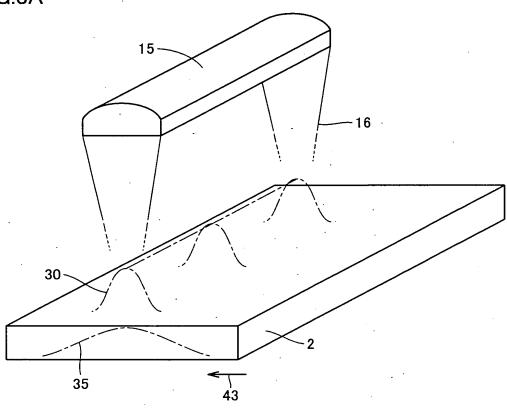
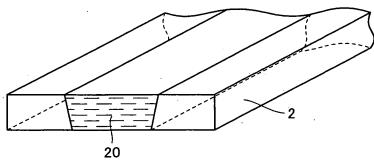


FIG.8B



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FIG.9

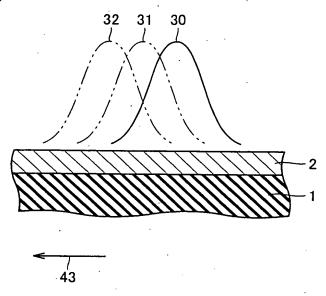


FIG.10A

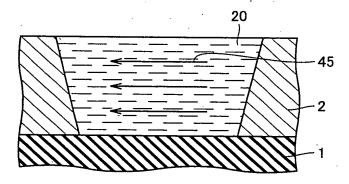
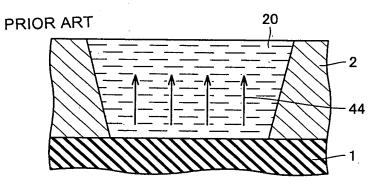


FIG.10B



30/531991

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FIG.11

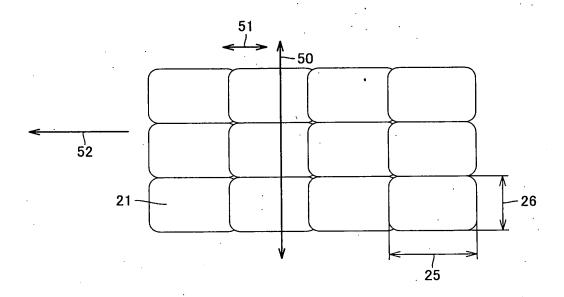
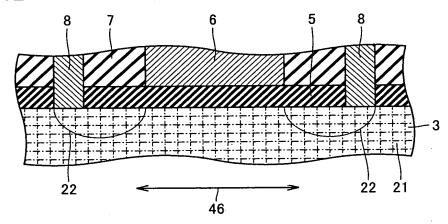


FIG.12

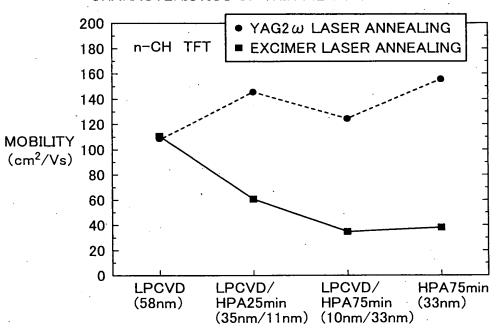


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FIG.13

CHARACTERISTICS OF THIN FILM TRANSISTORS



CONFIGURATION OF GATE INSULATING FILM

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FIG.14

